



# Proton radiation damage in SiPM for gamma-ray spectroscopy

30/11/2023 - A. PANGLOSSE<sup>1</sup>, A. MATERNE<sup>2</sup>, M. RUFFENACH<sup>2</sup>, J. CARRON<sup>2</sup>, C. AICARDI<sup>2</sup>, D. PAILOT<sup>3</sup>.

<sup>1</sup> EXPLEO Group, 13 rue Marie-Louise Dissard, 31300 Toulouse, France.

<sup>2</sup> Centre National d'Etudes Spatiales (CNES), 18 Avenue Édouard Belin, 31400 Toulouse, France.

<sup>3</sup> Laboratoire Astroparticule et Cosmologie (APC), 10 Rue Alice Domon et Léonie Duquet, 75013 Paris, France.

**RADOPT**



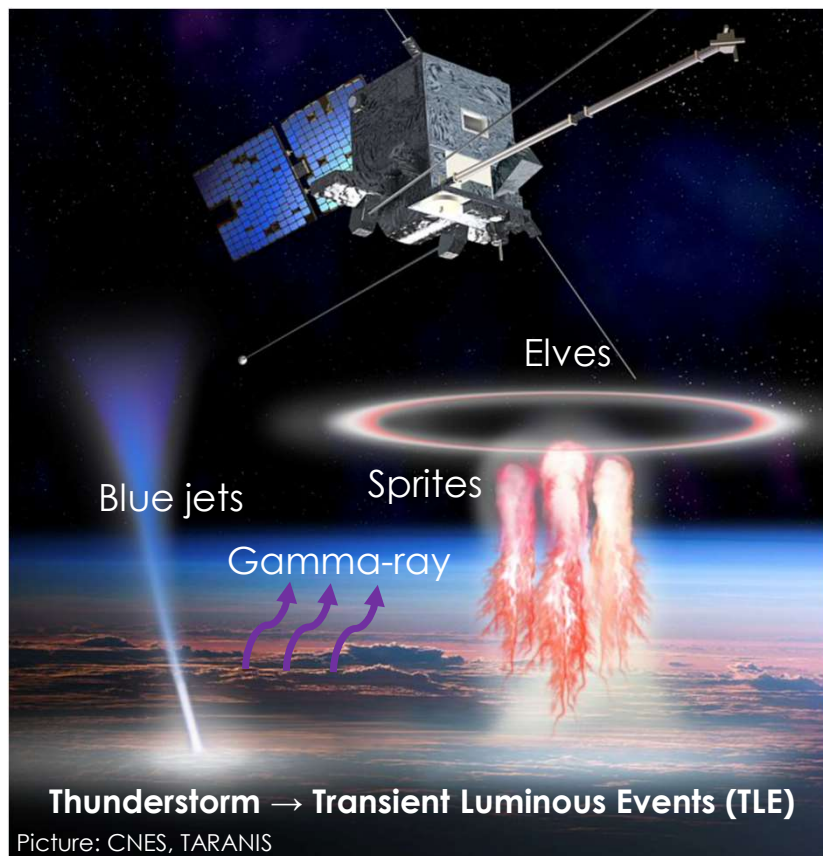
**( expleo )**

# Table of contents



- Introduction to the Fast Gamma-Ray Spectrometer (FGS)
- Experiment, proton irradiation on Silicon PhotoMultipliers (SiPM)
- Results, SiPM performance degradation with irradiation
- Impact on the spectrometer performances

# The Fast Gamma-ray Spectrometer (FGS)

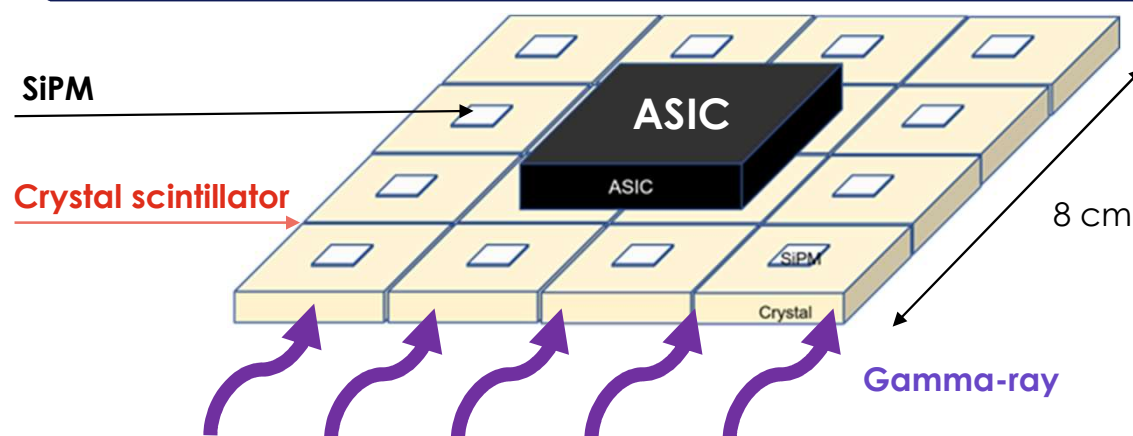


**CNES objective :** prepare future spaceborne **Gamma-Ray spectrometers** for **Terrestrial Gamma Ray Flash (TGF)** detection with promising, versatile, and more integrated technologies, while enhancing the Technology Readiness Level of the building blocks.

3 Proton radiation damage in SiPM for gamma-ray spectroscopy | © Expleo

**FGS** under development by APC and LESIA integrates :

- **Silicon Photomultipliers (SiPM) detectors;**
- GaGG:Ce scintillators;
- rad-hard 16 channels ASIC designed by IDEAS.



FGS detection module architecture featuring 1 ASIC with its 16 channels.

## Gamma-ray spectrometer requirements

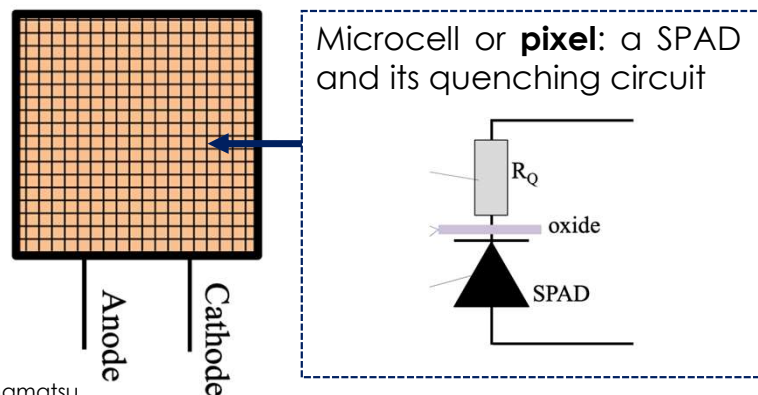
Maximum incident flux	$5 \times 10^4$ photons/cm <sup>2</sup> /s
Gamma photons dynamic range	20 keV – 20 MeV
Resolution	15% @ 511 keV

( expleo )

# The Silicon Photomultipliers (SiPM)

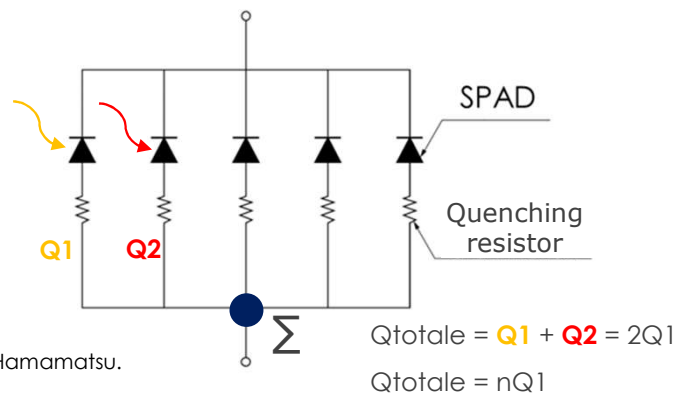
Detector composed of Single-Photon Avalanche Diodes (SPADs) implanted on a common substrate.

## Simplified diagram of a SiPM :

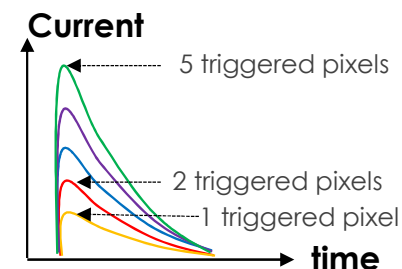


Source : Hamamatsu.

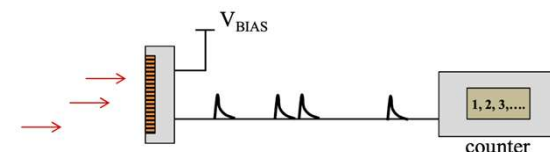
## Simplified circuit diagram of a SiPM :



Source : Hamamatsu.

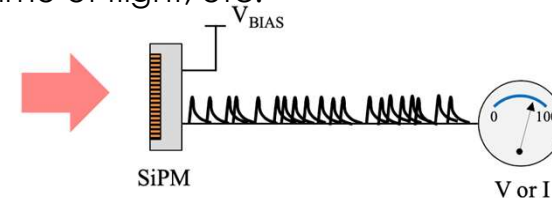


Summation of charges: output signal amplitude  $\sim$  number of triggered pixels (number of detected photons if efficiency = 1).



Source : Hamamatsu.

Distinguishable pulses: ability to count, measure the time intervals between events, time of flight, etc.



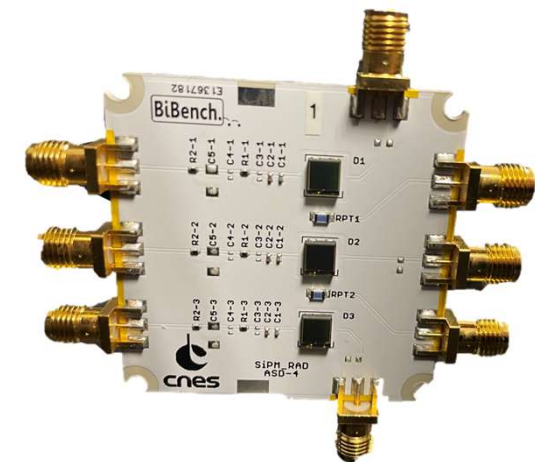
Source : Hamamatsu.

Ability to operate in analog mode, measuring either current or voltage.

( expleo )



# Experiment



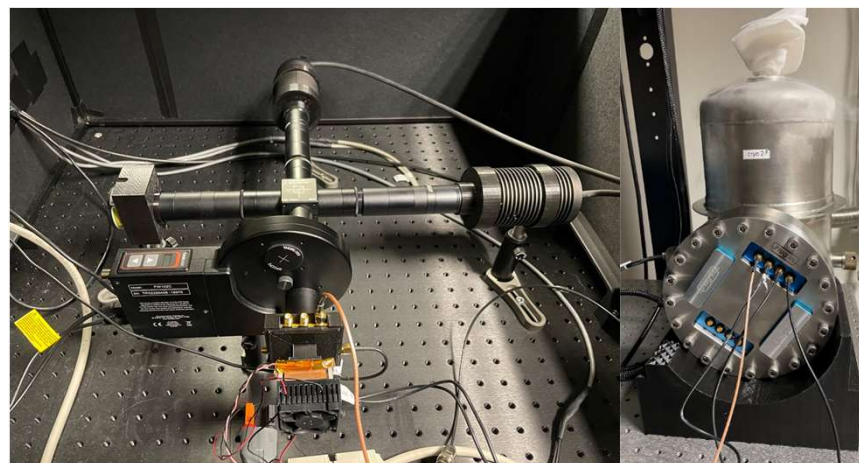
## Objective:

- **SiPM** end-of-life performance assessed through protons radiation campaign;
- evaluate the impact on the spectrometer **threshold energy** and **resolution**;
- select the best SiPM candidate and anticipate mitigating strategies such as low temperature regulation of the detectors;
- 3 references : **Advansid RGB4S-P**, **Onsemi FJ60035**, **Hamamatsu S13360-6050**.

## Irradiation:

- **62 MeV proton irradiation** at Université Catholique de Louvain (UCL);
- 2 years mission duration at 700 km  $\Rightarrow$  **fluence** :  $4 \times 10^9 \text{ p+}/\text{cm}^2$  with 10 mm aluminum shielding;
- fluence applied:  $1 \times 10^9$ ,  $4 \times 10^9$  and  $8 \times 10^9$ , with  $1 \times 10^7 \text{ p+}/\text{cm}^2/\text{s}$  flux.

	SiPM test plan		
	Initial	At UCL after protons	After ambient temperature annealing
I(V) @ 22°C	X	X	X
I(V) @ -20°C	X		X
Gain	X		X
Dark Count Rate DCR	X		
Photon Detection Efficiency PDE	X		X
Afterpulse	X		
Crosstalk	X		



SiPM testbench at CNES.

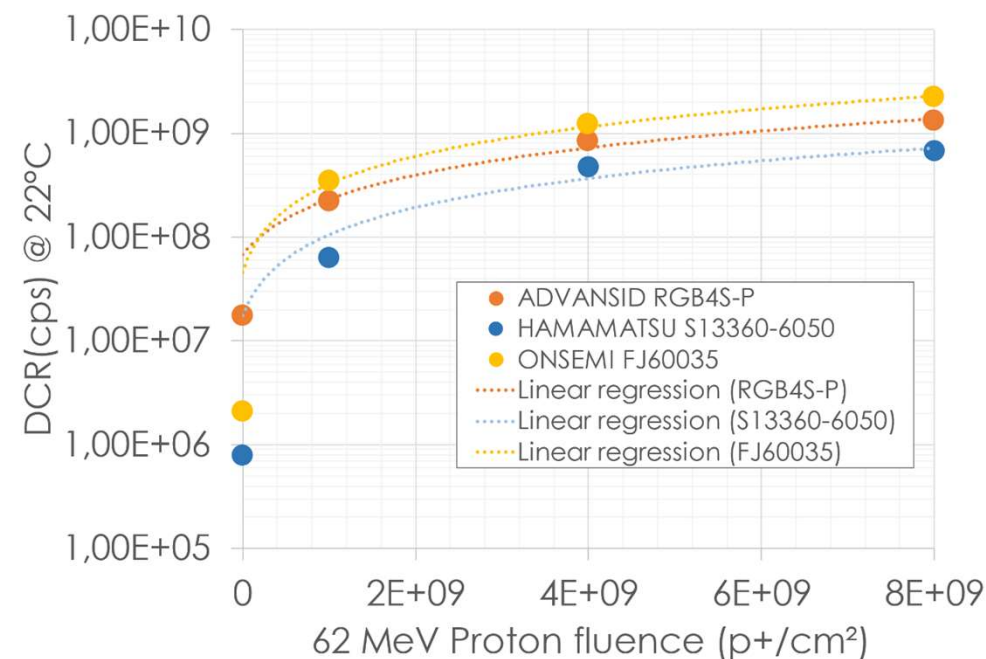
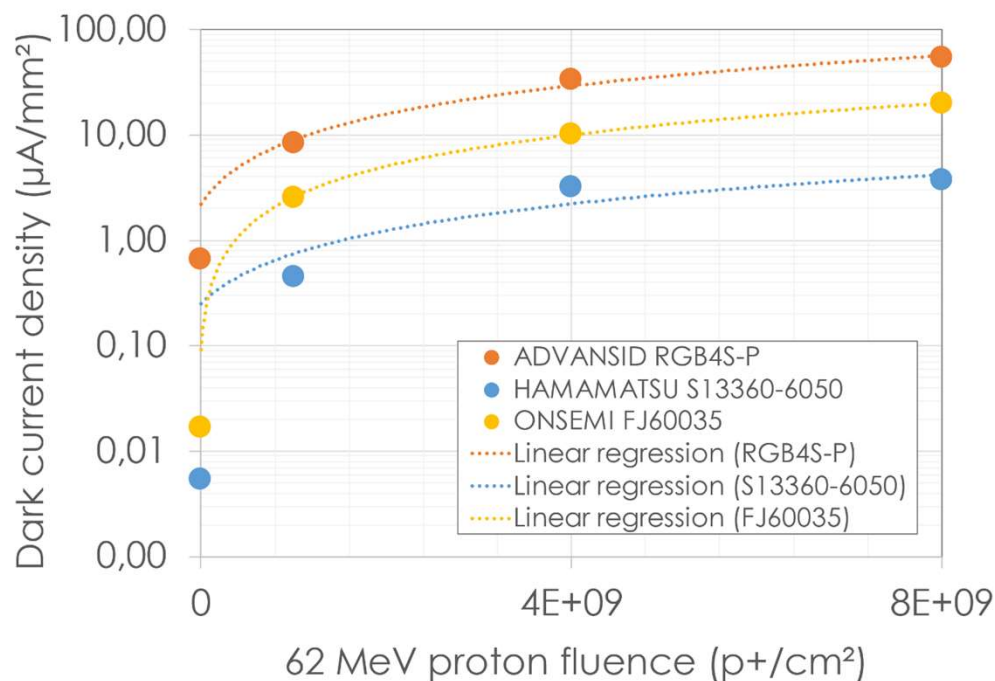


Irradiation facility at UCL.

**( expleo )**

# Results

- No significant change in measured gain and PDE after irradiation.



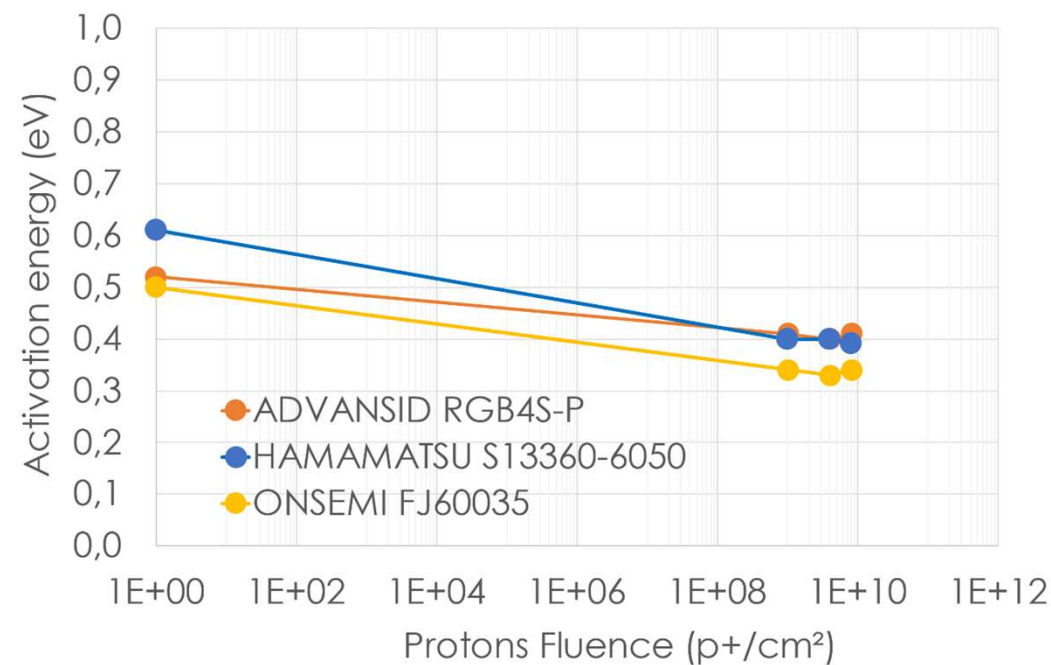
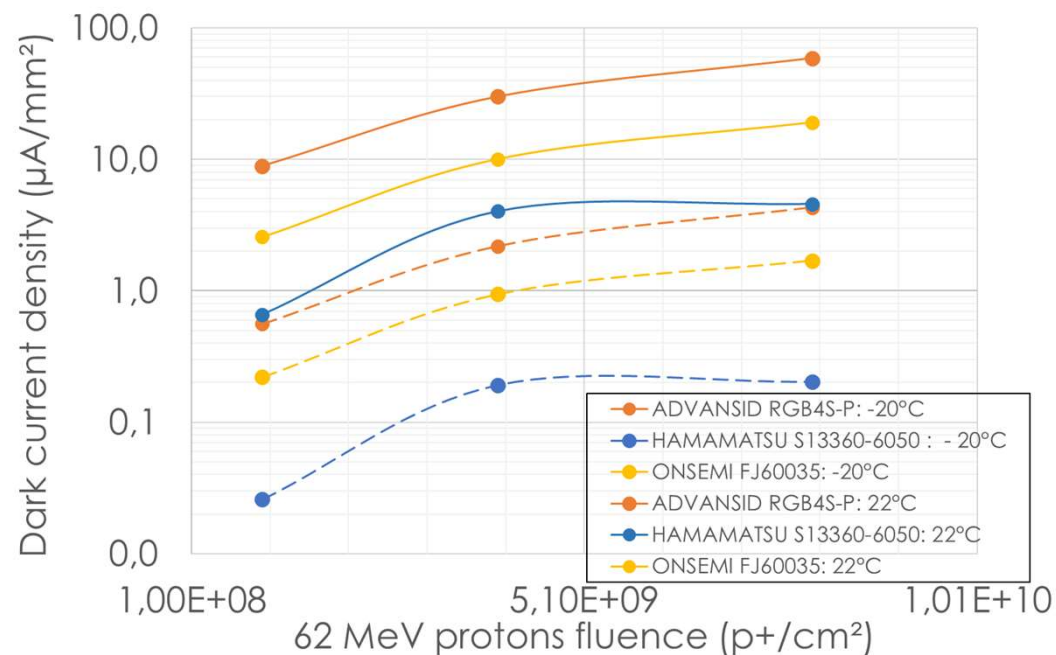
Approximation of the **Dark Count Rate**,  $DCR = \frac{I_{dark}}{q \times G \times ECF}$

$I_{dark}$ : dark current;  $q$ : elementary charges;  $G$ : gain;  $ECF$ : excess charge factor.

- Excess Charge Factor is not degraded by proton radiation, as reported by [1] and [2] for our range of fluences.

[1] P. Bohn, et al., "Radiation Damage Studies of Silicon Photomultipliers," *Nucl. Instrum. Methods Phys. Res., A*, pp. 722-736, 2009.  
 [2] E. Garutti and Y. Musienko, "Radiation damage of SiPMs," *Nuclear Instruments and Methods in Physics Research Section A*, pp. 69-84, 2019.

# Results



Activation energy from the comparison of measurements from -20°C to + 22°C.

## Observation:

- Increase of current after irradiation reduced by lowering the temperature.
- However, the decrease in activation energy with increasing proton fluence  $\Rightarrow$  the cooling efficiency also decreases.

( expleo )

# Impact on the spectrometer performance

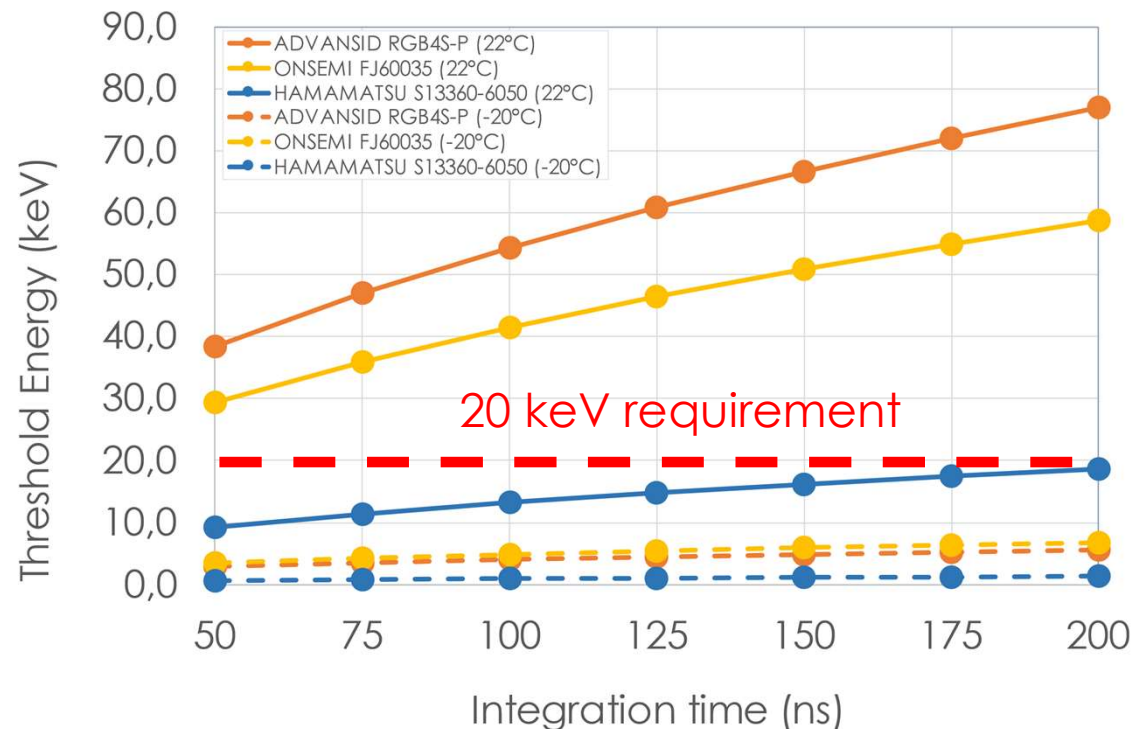
## Energy threshold:

$$E_{thres\_SiPM} = \frac{5 \times \sqrt{ENF \times DCR \times T_{int}}}{K_{lin}}$$

- One Gamma-Ray photon with energy **E<sub>γ</sub>** gives rise to **N<sub>pe</sub>** photoelectrons over the decay time of the scintillator;
- K<sub>lin</sub> : theoretical slope of the N<sub>pe</sub>(E<sub>γ</sub>) curve in the linear region;
- ENF : Excess Noise Factor;
- T<sub>int</sub> : integration time.

## Observation:

- DCR increases with radiations ⇒ increase in energy threshold.
- SiPM **HAMAMATSU 13360-6050** : only candidate to comply with the **20 keV threshold requirement at end-of-life for operating temperature at + 22°C**.
- SiPMs RGB4S-P and FJ60035 require cooling.



Contribution of DCR to the Energy threshold at end-of -life for  $8 \cdot 10^9$  p+/cm<sup>2</sup> 62 MeV proton radiation.

( expleo )



# Impact on the spectrometer performance

## Resolution:

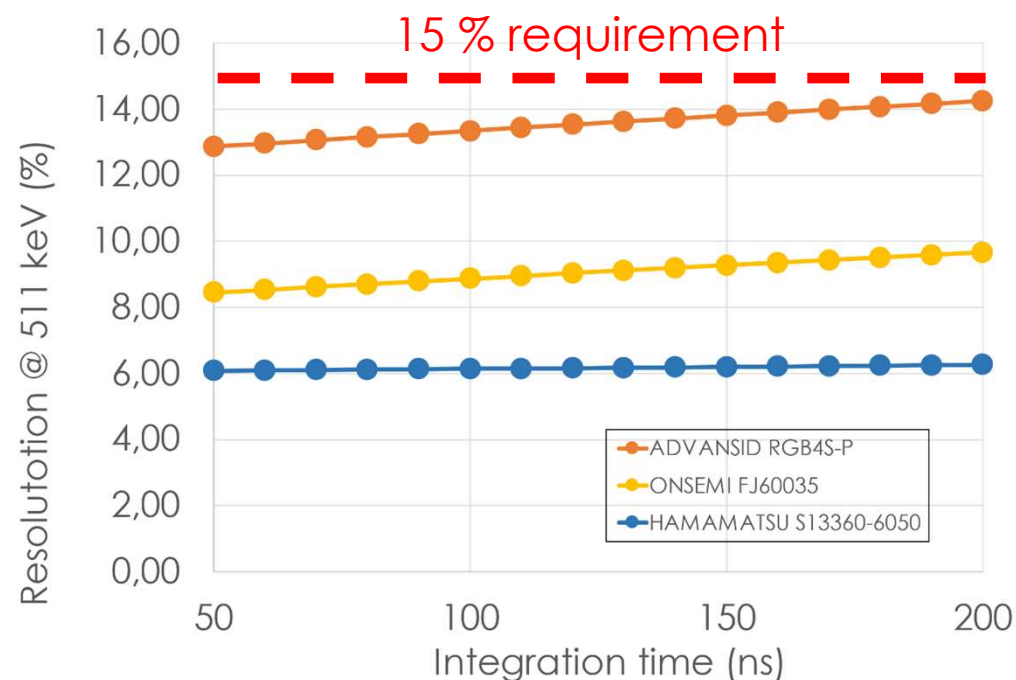
$$Resol_{511\text{ keV}_{SiPM}} = \frac{FWHM_{511\text{ keV}}}{511}$$

$$= 2 \times \sqrt{2 \times \ln 2} \times \frac{\sqrt{ENF \times (DCR \times T_{int} + N_{pe})}}{N_{pe}}$$

- One Gamma-Ray photon with energy **E<sub>γ</sub>** gives rise to **N<sub>pe</sub>** photoelectrons over the decay time of the scintillator;
- ENF : Excess Noise Factor;
- *T<sub>int</sub>* : integration time.

## Observation:

- DCR increases with radiations ⇒ enlargement of the energy resolution;
- Energy resolution at 511 keV is practically not affected by the DCR degradation with radiation. **The best result is obtained for SiPM HAMAMATSU S13360-6050.**



Resolution at 511 keV at 22°C end-of-life for  $8 \times 10^9$  p+/cm<sup>2</sup>, 62 MeV proton radiation.

( expleo )

# Conclusion

## Objective:

- The FGS instrument contains SiPM detectors; 3 references have been selected and need to be characterized to assess their radiation tolerance;
- For a satellite at an altitude of around 700 km for a 2 years mission duration, the main source of radiation that can damage the SiPMs is protons around 62 MeV with a fluence of  $4 \times 10^9 \text{ p}^+/\text{cm}^2$ .

## Main results:

- Characterizations show a degradation of dark current and DCR but no significant impacts on gain and PDE;
- DCR increases with radiations  $\Rightarrow$  increase in energy threshold and small enlargement of the energy resolution of the FGS spectrometer ;
- Only the **Hamamatsu S13360-6050** meets the specifications without the need to reduce the detector temperature.



Thank you for your attention!

(expleo)

Think bold, act reliable\*

**Aymeric Panglosse, Ph.D.**

• Toulouse • France

[aymeric.panglosse@expleogroup.com](mailto:aymeric.panglosse@expleogroup.com)

**RADOPT**



**cnes**  
CENTRE NATIONAL  
D'ÉTUDES SPATIALES

\* Osons l'audace, créons la confiance

[expleogroup.com](http://expleogroup.com)